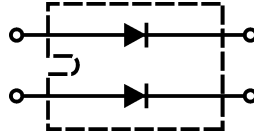


# Fast Recovery Epitaxial Diode (FRED)

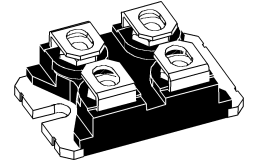
## DSEI 2x 61

$I_{FAVM} = 2x 52 A$   
 $V_{RRM} = 1200 V$   
 $t_{rr} = 40 ns$

$V_{RSM}$ V	$V_{RRM}$ V	Type
1200	1200	DSEI 2x 61-12B



miniBLOC, SOT-227 B  
 E72873



Symbol	Test Conditions	Maximum Ratings (per diode)	
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	100	A
$I_{FAVM}$ ①	$T_C = 50^\circ C$ ; rectangular, $d = 0.5$	52	A
$I_{FRM}$	$t_p < 10 \mu s$ ; rep. rating, pulse width limited by $T_{VJM}$	700	A
$I_{FSM}$	$T_{VJ} = 45^\circ C$ ; $t = 10 ms$ (50 Hz), sine	450	A
	$t = 8.3 ms$ (60 Hz), sine	500	A
	$T_{VJ} = 150^\circ C$ ; $t = 10 ms$ (50 Hz), sine	400	A
	$t = 8.3 ms$ (60 Hz), sine	440	A
$I^2t$	$T_{VJ} = 45^\circ C$ ; $t = 10 ms$ (50 Hz), sine	1000	A <sup>2</sup> s
	$t = 8.3 ms$ (60 Hz), sine	1050	A <sup>2</sup> s
	$T_{VJ} = 150^\circ C$ ; $t = 10 ms$ (50 Hz), sine	800	A <sup>2</sup> s
	$t = 8.3 ms$ (60 Hz), sine	810	A <sup>2</sup> s
$T_{VJ}$		-40...+150	°C
$T_{VJM}$		150	°C
$T_{stg}$		-40...+150	°C
$P_{tot}$	$T_C = 25^\circ C$	180	W
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	2500	V~
$M_d$	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
<b>Weight</b>		30	g

### Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 2500 V~
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{FRM}$ -values
- Soft recovery behaviour

### Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
$I_R$	$T_{VJ} = 25^\circ C$ ; $V_R = V_{RRM}$		2.2 mA
	$T_{VJ} = 25^\circ C$ ; $V_R = 0.8 \cdot V_{RRM}$		0.5 mA
	$T_{VJ} = 125^\circ C$ ; $V_R = 0.8 \cdot V_{RRM}$		14 mA
$V_F$	$I_F = 60 A$ ; $T_{VJ} = 150^\circ C$ $T_{VJ} = 25^\circ C$		2.15 V
			2.50 V
$V_{T0}$	For power-loss calculations only		1.65 V
$r_T$	$T_{VJ} = T_{VJM}$		8.3 mΩ
$R_{thJC}$		0.7	K/W
$R_{thCK}$		0.05	K/W
$t_{rr}$	$I_F = 1 A$ ; $-di/dt = 200 A/\mu s$ ; $V_R = 30 V$ ; $T_{VJ} = 25^\circ C$	40	60 ns
$I_{RM}$	$V_R = 540 V$ ; $I_F = 60 A$ ; $-di_F/dt = 480 A/\mu s$ $L \leq 0.05 \mu H$ ; $T_{VJ} = 100^\circ C$	32	36 A

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$   
Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

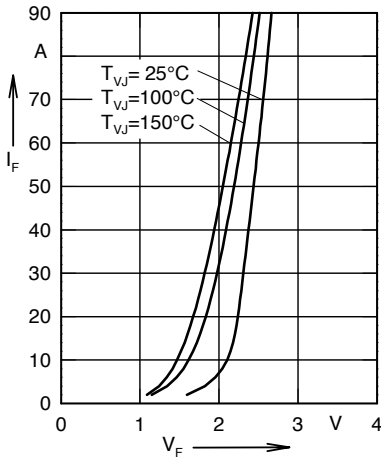


Fig. 1 Forward current versus voltage drop.

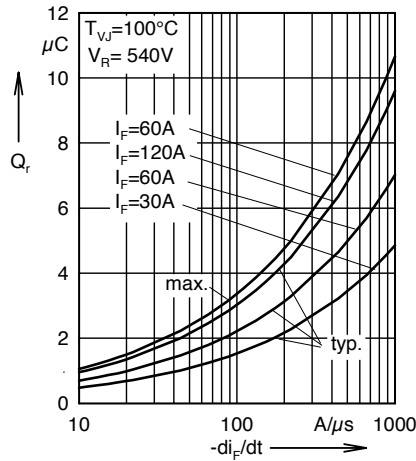


Fig. 2 Recovery charge versus  $-di_F/dt$ .

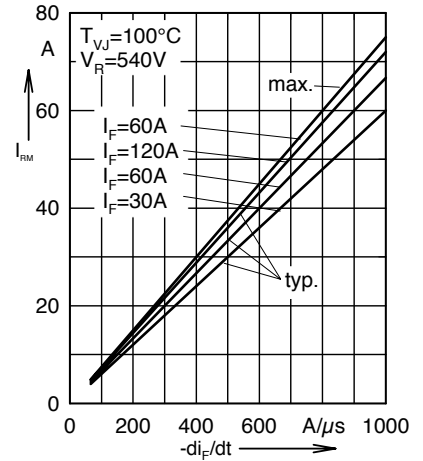


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

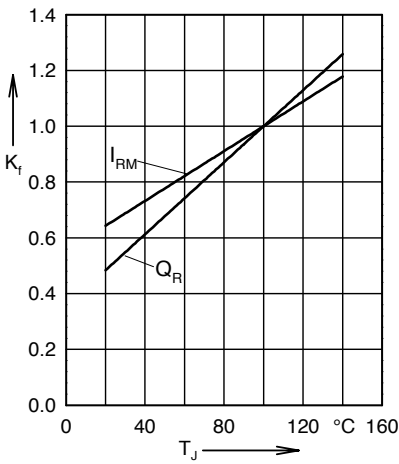


Fig. 4 Dynamic parameters versus junction temperature.

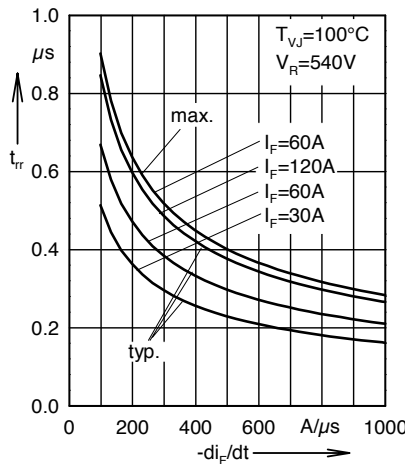


Fig. 5 Recovery time versus  $-di_F/dt$ .

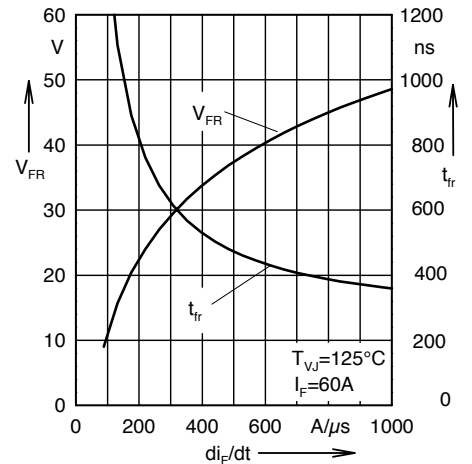


Fig. 6 Peak forward voltage versus  $di_F/dt$ .

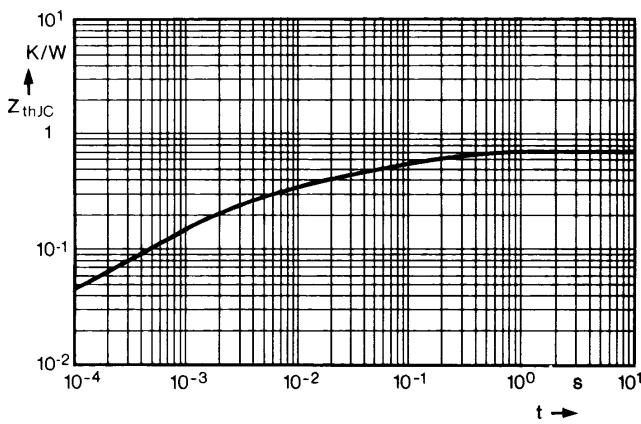
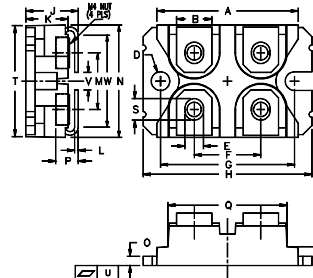


Fig. 7 Transient thermal impedance junction to case.

### Dimensions



miniBLOC SOT-227 B  
M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033